

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	49	("5853653" "6133159" "6380105" "5942064" "5985770" "6156674" "6304309" "6387514" "6868873" "5468978" "5532071" "5658834" "5874014" "6103015" "6331494" "6376391" "4894351" "5621062" "5750415" "5793457" "5995191" "6606780" "6699819" "6733715" "4911781" "5595603" "5966499" "4431848" "5336522" "5705283" "6208234" "6210592" "6210592" "4278458" "4613544" "5185298" "5206207" "5236874" "5262203" "5306447" "5326847" "5420085" "5468918" "5470424" "5492724" "5601769" "5783290" "5820678" "5997956" "5997642").pn.	US-PGPUB; USPAT	OR	OFF	2005/08/20 12:46
S2	50	("6158244" "6179925" "6183583" "6204402" "6207522" "4303731" "4303432" "4413069" "4415545" "4435272" "4532091" "4559010" "4578287" "4778626" "4782040" "4833026" "4871587" "4890574" "4900531" "4957780" "4993361" "5007476" "5032450" "5196235" "5221558" "5233165" "5246736" "5252831" "5269966" "5281514" "5290491" "5296171" "5306554" "5318761" "5328878" "5346852" "5348598" "5350738" "5352484" "5447569" "5456945" "5468357" "5476685" "5480676" "5486379" "5492718" "5512330" "5516734" "5534066" "5540772").pn.	US-PGPUB; USPAT	OR	OFF	2005/08/20 13:24
S3	5777	438/428.ccls. 438/436.ccls. 438/674.ccls. 438/681.ccls. 438/685.ccls. 438/687.ccls. 438/688.ccls. 438/763.ccls. 438/778.ccls. 438/782.ccls. 438/790.ccls.	US-PGPUB; USPAT	OR	OFF	2005/08/20 16:12
S4	412	438/428.ccls. 438/436.ccls. 438/674.ccls.	US-PGPUB; USPAT	OR	OFF	2005/08/20 14:28
S5	44	Kelvin adj effect	US-PGPUB; USPAT	OR	ON	2005/08/20 13:44
S6	59	Kelvin adj effect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 14:06

S7	302	S3 and ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) same liqui\$10)	US-PGPUB; USPAT	OR	ON	2005/08/20 16:15
S8	200	S3 and ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) same liqui\$10 same (precursor solid vapor condens\$8 fill\$6))	US-PGPUB; USPAT	OR	ON	2005/08/20 16:24
S9	4707	(substrate semiconductor wafer silicon) same (gap trench groove inlaid damascene "in-laid" slot recess concav\$6) same (liqui\$10 with (precursor solid vapor condens\$8 fill\$6))	US-PGPUB; USPAT	OR	ON	2005/08/20 16:18
S10	3234	(substrate semiconductor wafer silicon) same ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) with liqui\$10 with (precursor solid vapor condens\$8 fill\$6))	US-PGPUB; USPAT	OR	ON	2005/08/20 16:20
S13	1	"6300219".pn.	US-PGPUB; USPAT	OR	OFF	2005/08/20 16:24
S14	125	(substrate semiconductor wafer silicon) same ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) with liqui\$10 with (precursor solid vapor condens\$8) with (selectiv\$6 fill\$6))	US-PGPUB; USPAT	OR	ON	2005/08/22 07:42
S15	228	(substrate semiconductor wafer silicon) and (gap trench groove inlaid damascene "in-laid" slot recess concav\$6) and liqui\$10 and (precursor solid vapor condens\$8) and (selectiv\$6 fill\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 07:42